IN THE SPECIFICATION:

Please amend the paragraph beginning at page 23, line 21, and ending at page 24, line 2, as follows:

Fig. 6 shows a side view of a section of probe card 74 and a die 16. The section shown typically is in an edge region of probe card 74 and includes three mechanical connections to the top of the probe card. In the preferred embodiment, probe card 74 extends across the full diameter 12 of wafer 10 so that a single probe card is used for simultaneously powering on and off all the die on the wafer during simultaneous burn-in of each die on the wafer.

Please amend the paragraph beginning at page 24, line 14, and ending at page 24, line 22, as follows:

Power source layer 110 includes a switch 120 movable between the on (closed) and the off (open) positions so as to control power to the entire probe card. In the preferred embodiment, switch 120 is an optical switch that moves between the open and the closed positions when a light signal is applied to the switch. Switch 120 is directly connected to layer 110 and extends through the entire depth of layer 110 so that the remainder of layer 110 is only powered when switch 120 is in the on position. Accordingly, switch 120 is the main control switch for simultaneously providing power to each all the die on wafer 10.

Please amend the paragraph beginning at page 25, line 17, and ending at page 26, line 4, as follows:

Signal layer 114 is electrically connected to an electrically conductive bump 130 by an electrical lead 132 that extends from a signal switch 134. Lead 132 is electrically isolated from ground layer 118 by an isolation barrier 136 and switch 134 is electrically isolated from power source layer 110 by an isolation barrier 138. Barrier 136 also electrically isolates bump 130 from ground layer 118. Bumps 124 and 130, and leads 122 and 132 are manufactured of an electrically conductive material, such as gold, though other materials may be used. Those skilled in the art will understand that the isolation barriers surround the electrical leads but generally do not extend through the entire cross section of the probe card layer. Lead 132 is electrically connected to metallic signal source layer 114 so that each of the die on wafer 10 is electrically connected in parallel to the signal layer, providing for simultaneous electrical connection of all the die on the wafer to signal layer 114.